SN74LV10A トリプル 3 入力正論理 NAND ゲート

1 特長

- 2V～5.5V の V_{CC} で動作
- 最大 t_{pd} 7ns (5V 時)
- 標準 V_{OLP} (出力グランド・バウンス) < 0.8V (V_{CC} = 3.3V、T_A = 25℃)
- 標準 V_{OHV} (出力 V_{OH} アンダーシュート) > 2.3V (V_{CC} = 3.3V、TA = 25℃)
- I_{off} により部分的パワーダウン・モード動作をサポート
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能

2 アプリケーション

- アラーム / タンパ検出回路
- S-R ラッチ

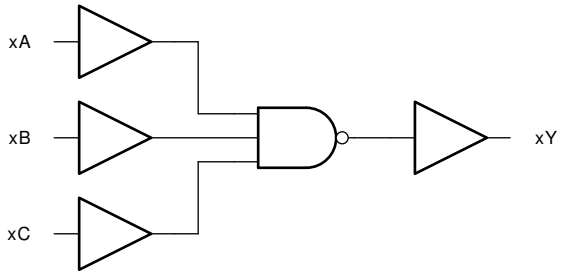
3 説明

これらのトリプル 3 入力正論理 NAND ゲートは、2V～5.5V V_{CC} 動作に向けて設計されています。SN74LV10A デバイスはブール関数 $Y = \overline{A \cdot B \cdot C}$ を正論理で実行します。これらのデバイスは、I_{off} を使用する部分的パワーダウン・アプリケーション用の動作が完全に規定されています。I_{off} 回路が出力をディスエーブルにするので、電源切断時にデバイスに電流が逆流して損傷に至ることを回避できます。

パッケージ情報(1)

部品番号	パッケージ(1)	本体サイズ (公称)
SN74LV10A	D (SOIC、14)	8.65mm × 3.90mm
	NS (SO、14)	10.20mm × 5.30mm
	PW (TSSOP、14)	5.00mm × 4.40mm

(1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



簡略回路図

Table of Contents

4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision F (May 2022) to Revision G (March 2023) **Page**

- ドキュメントの構造レイアウトを現行の標準に更新、「アプリケーション」セクションを追加、「パッケージ情報」表を更新 1

Changes from Revision E (April 2015) to Revision F (May 2022) **Page**

- 最新のデータシート規格を反映するように、文書全体にわたって採番方式、書式、表、図、相互参照を更新 ... 1

5 Pin Configuration and Functions

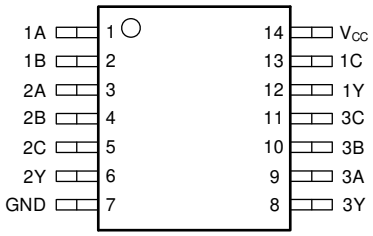


図 5-1. SN74LV10A . . . D, NS, or PW Package (Top View)

表 5-1. Pin Functions

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
1A	1	I	1A Input
1B	2	I	1B Input
NC	3	—	Not internally connected
1C	4	I	1C Input
1D	5	I	1D Input
1Y	6	O	1Y Output
2Y	8	O	2Y Output
2A	9	I	2A Input
2B	10	I	2B Input
NC	11	—	Not internally connected
2C	12	I	2C Input
2D	13	I	2D Input
GND	7	—	Ground Pin
V_{CC}	14	—	Power Pin

(1) Signal Types: I = Input, O = Output.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7	V
V_I	Input voltage range(2)		–0.5	7	V
V_O	Output voltage range applied in high or low state(2) (3)		–0.5	V_{CC} + 0.5	V
V_O	Output voltage range applied in power-off state(2)		–0.5	7	V
I_{IK}	Input clamp current	(V_I < 0)		–20	mA
I_{OK}	Output clamp current	(V_O < 0)		–50	mA
I_O	Continuous output current	(V_O = 0 to V_{CC})		±25	mA
	Continuous current through V_{CC} or GND			±50	mA
θ_{JA}	Package thermal impedance			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) This value is limited to 5.5 V maximum.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	± 2000	V
		Machine Model, per JEDEC specification	± 200	
		Charged device model (CDM), per JEDEC specification JS-002 (2)	± 1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		2	5.5	V
V_{IH}	High level input voltage	V_{CC} = 2 V	1.5		V
		V_{CC} = 2.3 V to 2.7 V	V_{CC} × 0.7		
		V_{CC} = 3 V to 3.6 V	V_{CC} × 0.7		
		V_{CC} = 4.5 V to 5.5 V	V_{CC} × 0.7		
V_{IL}	Low level input voltage	V_{CC} = 2 V		0.5	V
		V_{CC} = 2.3 V to 2.7 V		V_{CC} × 0.3	
		V_{CC} = 3 V to 3.6 V		V_{CC} × 0.3	
		V_{CC} = 4.5 V to 5.5 V		V_{CC} × 0.3	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High level output current	V_{CC} = 2 V		–50	μA
		V_{CC} = 2.3 V to 2.7 V		–2	mA
		V_{CC} = 3 V to 3.6 V		–6	
		V_{CC} = 4.5 V to 5.5 V		–12	

6.3 Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
I_{OL}	Low level output current	V_{CC} = 2 V		50	μA
		V_{CC} = 2.3 V to 2.7 V		2	mA
		V_{CC} = 3 V to 3.6 V		6	
		V_{CC} = 4.5 V to 5.5 V		12	
Δt/Δv	Input transition rise and fall rate	V_{CC} = 2.3 V to 2.7 V		200	ns/V
		V_{CC} = 3 V to 3.6 V		100	
		V_{CC} = 4.5 V to 5.5 V		20	
T_A	Operating free-air temperature		–40	85	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs,* literature number SCBA004

6.4 Thermal Information

THERMAL METRIC(1)		SN74LV10A			UNIT
		D	NS	PW	
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	86	76	113	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report (SPRA953).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –50 μA	2 V to 5.5 V	V_{CC} - 0.1			V
		I_{OH} = –2 mA	2.3 V	2			
		I_{OH} = –6 mA	3 V	2.48			
		I_{OH} = –12 mA	4.5 V	3.8			
V_{OL}	Low-level output voltage	I_{OL} = 50 μA	2 V to 5.5 V			0.1	V
		I_{OL} = 2 mA	2.3 V			0.4	
		I_{OL} = 6 mA	3 V			0.44	
		I_{OL} = 12 mA	4.5 V			0.55	
I_I	Input leakage current	V_I = 5.5 V or GND	0 to 5.5 V			±1	μA
I_{CC}	Supply current	V_I = V_{CC} or GND, I_O = 0	5.5 V			20	μA
C_i	Input capacitance	V_I = V_{CC} or GND	3.3 V		1.9		pF

6.6 Switching Characteristics, V_{CC} = 2.5 V ± 0.2 V

over recommended operating free-air temperature range (unless otherwise noted) (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74LV10A		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	C_L = 15 pF		7.1	13	1	15.5	ns
t_{pd}	A, B, or C	Y	C_L = 50 pF		10.3	17.1	1	20.5	

6.7 Switching Characteristics, V_{CC} = 3.3 V ± 0.3 V

over recommended operating free-air temperature range (unless otherwise noted) (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74LV10A		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	C_L = 15 pF		5.2	8.4	1	10	ns
t_{pd}	A, B, or C	Y	C_L = 50 pF		7.4	11.9	1	13.5	

6.8 Switching Characteristics, V_{CC} = 5 V ± 0.5 V

over recommended operating free-air temperature range (unless otherwise noted) (see 図 7-1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	T_A = 25°C			SN74LV10A		UNIT
				MIN	TYP	MAX	MIN	MAX	
t_{pd}	A, B, or C	Y	C_L = 15 pF		3.9	5.9	1	7	ns
t_{pd}	A, B, or C	Y	C_L = 50 pF		5.4	7.9	1	9	

6.9 Noise Characteristics

V_{CC} = 3.3 V, C_L = 50 pF, T_A = 25°C

PARAMETER(1)		MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.2	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}		0	–0.8	V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}		3.2		V
$V_{IH(D)}$	High-level dynamic input voltage	2.31			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.99	V

(1) Characteristics are for surface-mount packages only.

6.10 Operating Characteristics

T_A = 25°C

PARAMETER		TEST CONDITIONS		V_{CC}	TYP	UNIT
C_{pd}	Power dissipation capacitance	C_L = 50 pF,	f = 10 MHz	3.3 V	14	pF
				5 V	16.7	

7 Parameter Measurement Information

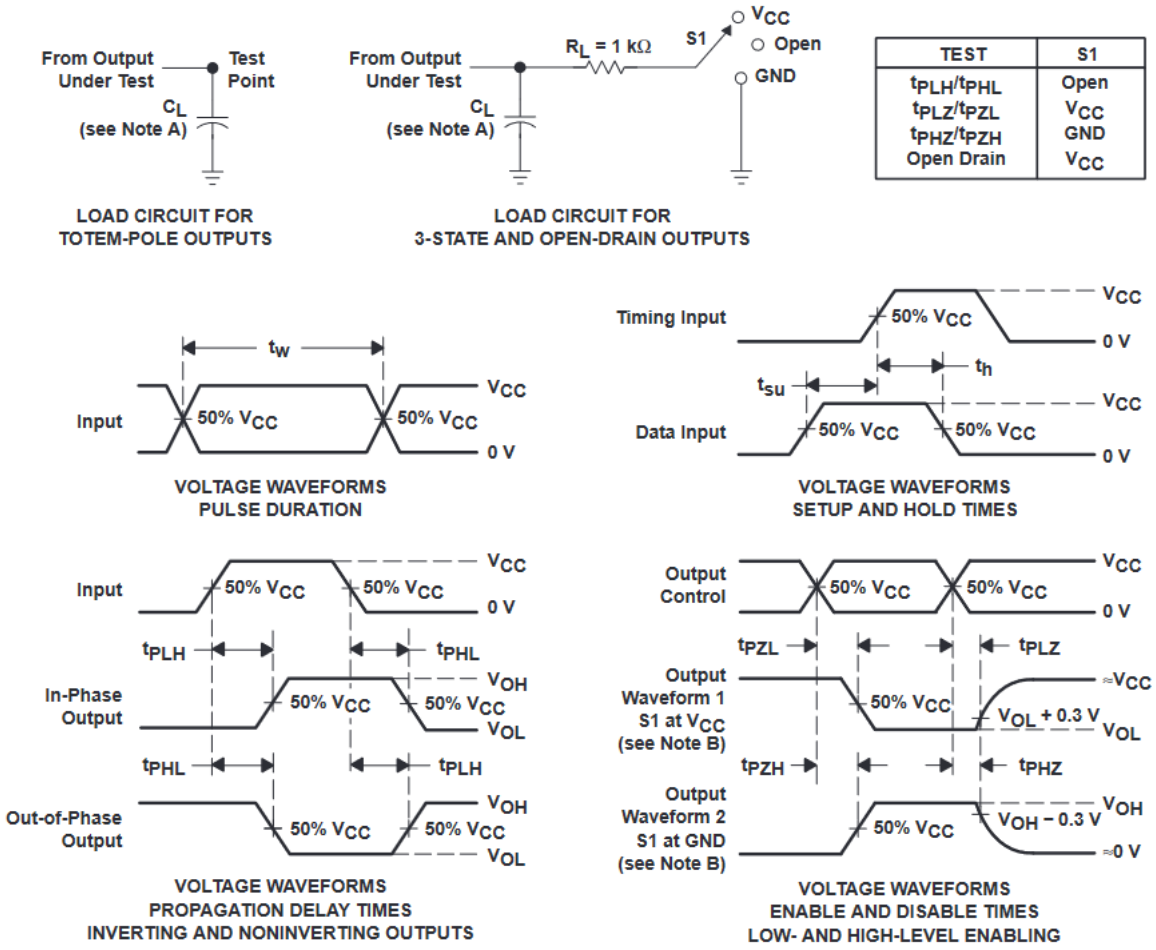


図 7-1. Load Circuit and Voltage Waveforms

A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r ≤ 3 ns, t_f ≤ 3 ns.
D. The outputs are measured one at a time, with one input transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PHL} and t_{PLH} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

8 Detailed Description

8.1 Overview

These triple 3-input positive-NAND gates are designed for 2-V to 5.5-V V_{CC} operation. The SN74LV10A devices perform the Boolean function $Y = \overline{A \cdot B \cdot C}$ in positive logic. These devices are fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down.

8.2 Functional Block Diagram

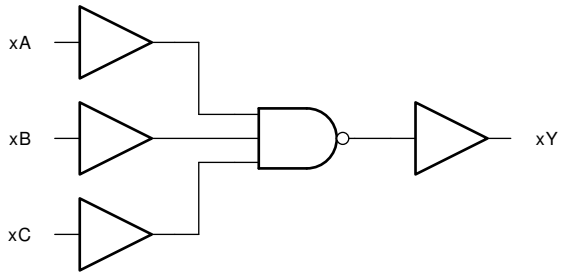


図 8-1. Simplified Schematic

8.3 Device Functional Modes

表 8-1. FUNCTION TABLE (each gate)

INPUT(1)			OUTPUT (2)
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care
(2) H = Driving High, L = Driving Low

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the Recommended Operating Conditions. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results.

9.2 Layout

9.2.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

10 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

10.1 Documentation Support

10.1.1 Related Documentation

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

表 10-1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
SN74LV10A	Click here	Click here	Click here	Click here	Click here

10.2 ドキュメントの更新通知を受け取る方法

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10.3 サポート・リソース

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10.6 用語集

テキサス・インスツルメンツ用語集　　この用語集には、用語や略語の一覧および定義が記載されています。

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LV10ADR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples
SN74LV10ADRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples
SN74LV10ANSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	74LV10A	Samples
SN74LV10APWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 85	LV10A	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

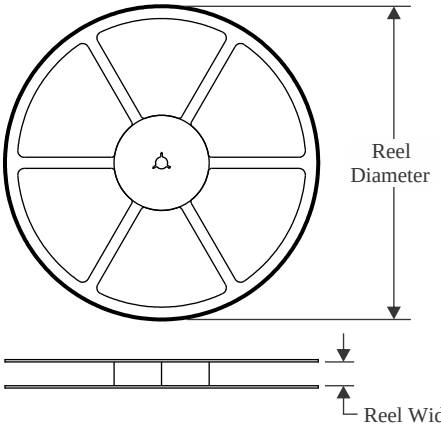
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals.
TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

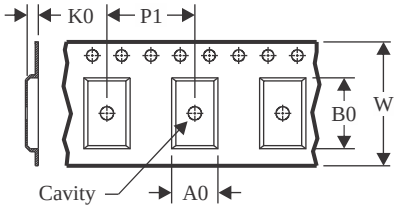
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

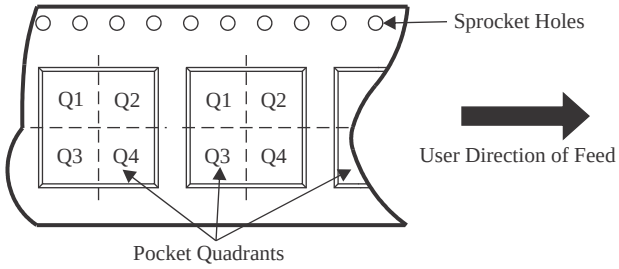


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

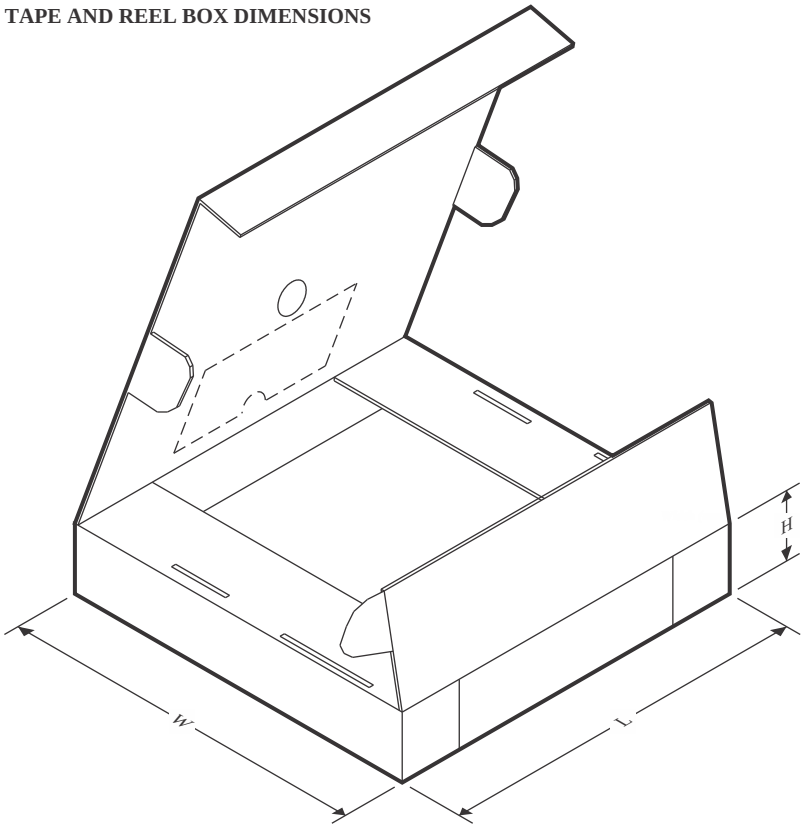
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LV10ADR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74LV10ANSR	SO	NS	14	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN74LV10APWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV10APWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74LV10APWR	TSSOP	PW	14	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



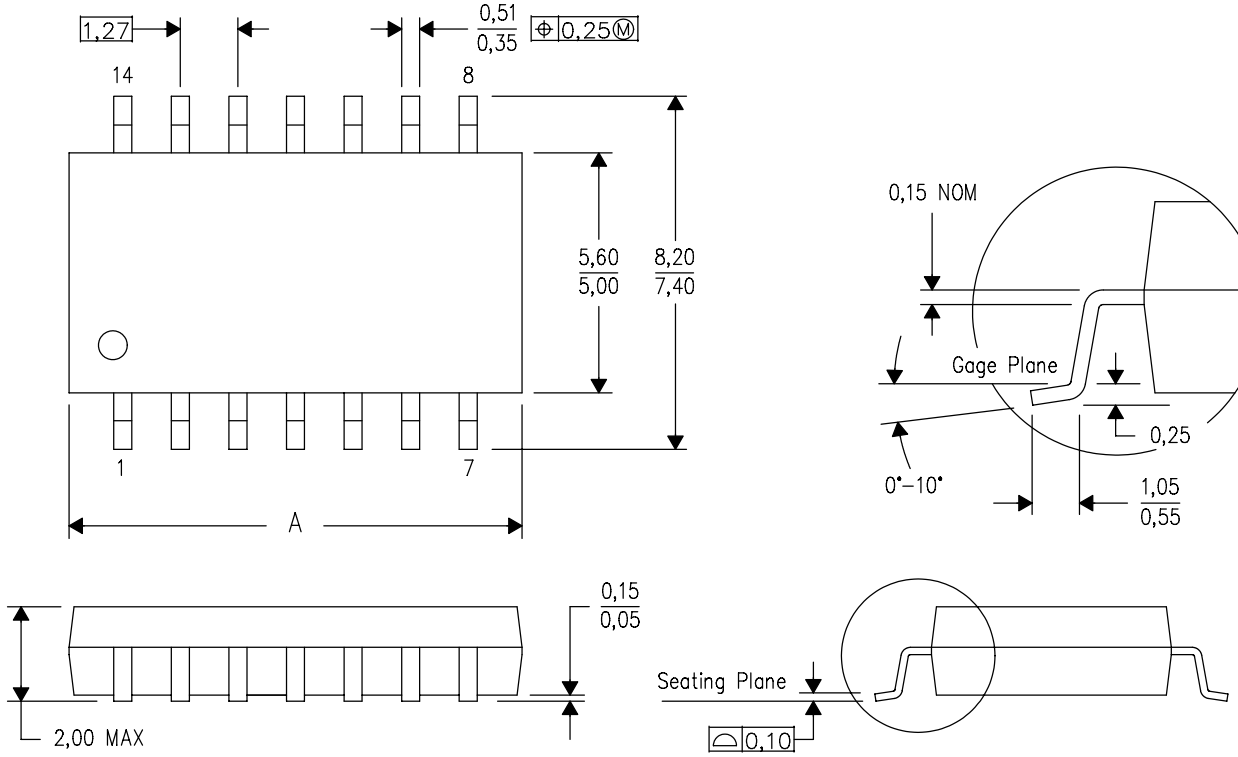
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LV10ADR	SOIC	D	14	2500	356.0	356.0	35.0
SN74LV10ANSR	SO	NS	14	2000	356.0	356.0	35.0
SN74LV10APWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74LV10APWR	TSSOP	PW	14	2000	353.0	353.0	32.0
SN74LV10APWR	TSSOP	PW	14	2000	366.0	364.0	50.0

MECHANICAL DATA

NS (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14-PINS SHOWN

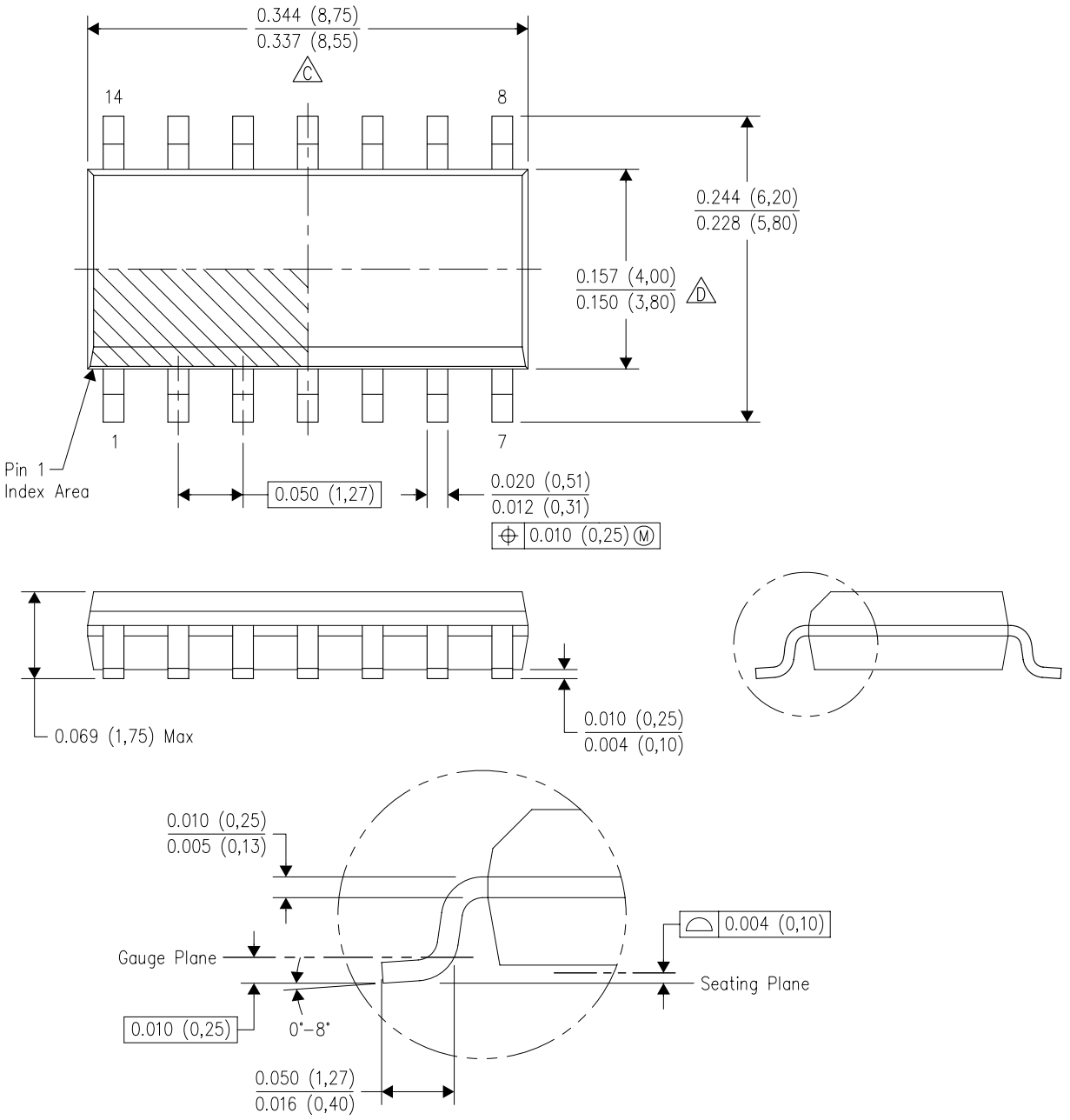


DIM \ PINS **	14	16	20	24
A MAX	10,50	10,50	12,90	15,30
A MIN	9,90	9,90	12,30	14,70

4040062/C 03/03

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.

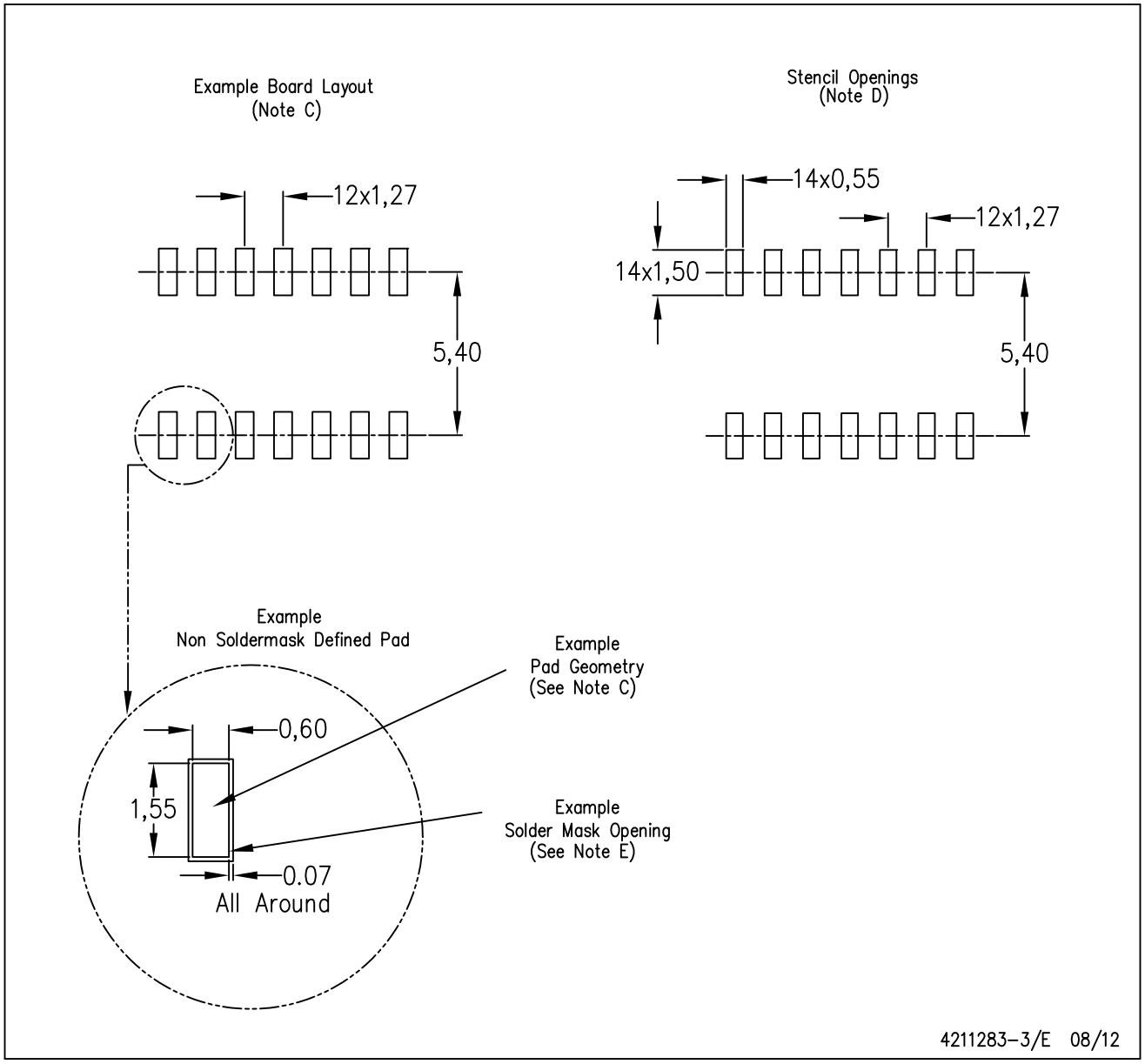
D (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040047–5/M 06/11

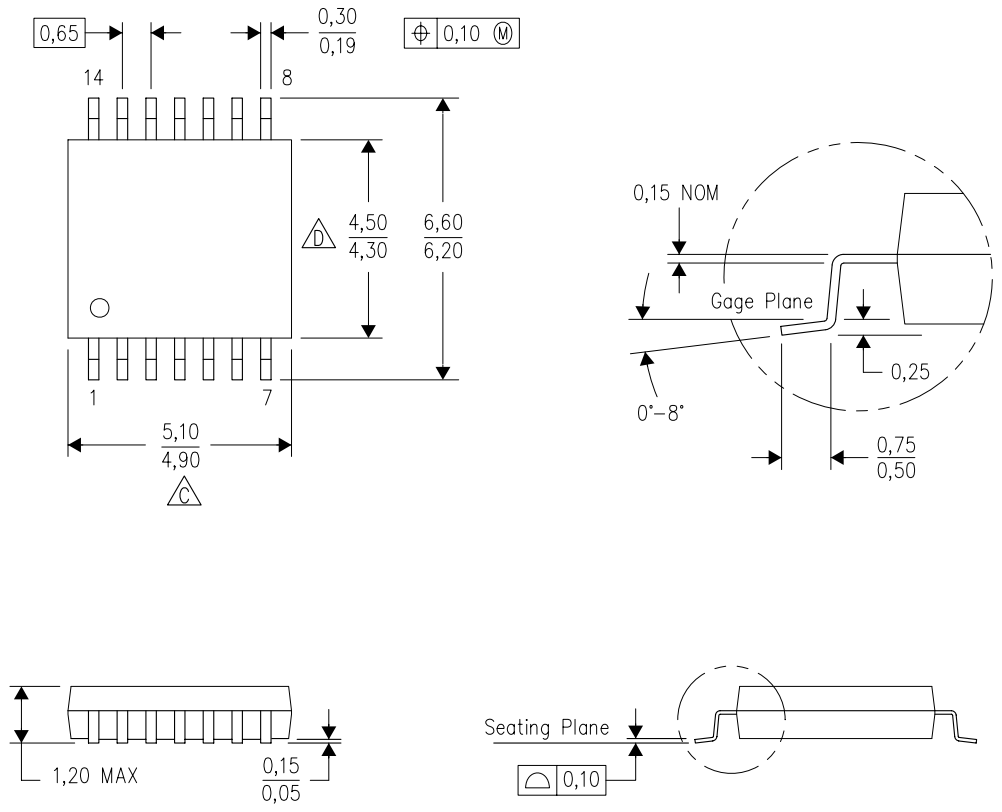
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AB.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

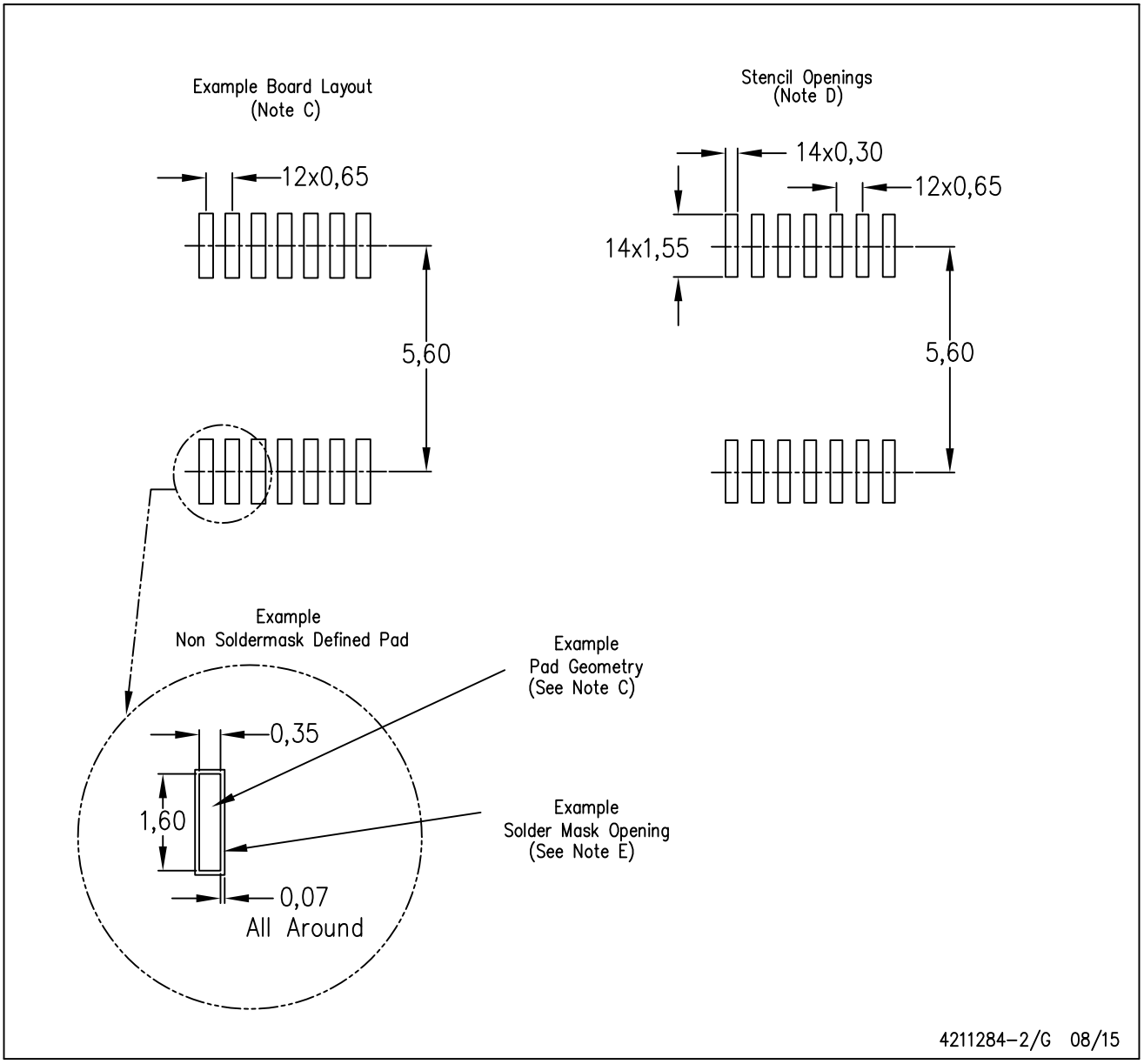
PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



4040064–3/G 02/11

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R–PDSO–G14) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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